

PMF63UNE 20 V, N-channel Trench MOSFET 20 April 2016

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- LED driver
- Power management
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	2.2	А
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 2 \text{ A}; T_j = 25 \text{ °C}$		-	57	65	mΩ

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	□ 3	D I
2	S	souce		
3	D	drain	1 2 SC-70 (SOT323)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMF63UNE	SC-70	plastic surface-mounted package; 3 leads	SOT323			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMF63UNE	Z%V

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	2.2	Α
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	2	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	1.3	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	8	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	300	mW
			[1]	-	395	mW
		T _{sp} = 25 °C		-	1.8	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
I _S	source current	T _{amb} = 25 °C	[1]	-	0.37	Α

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.

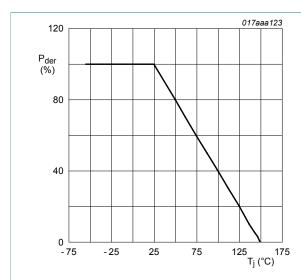


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

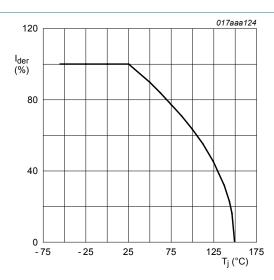


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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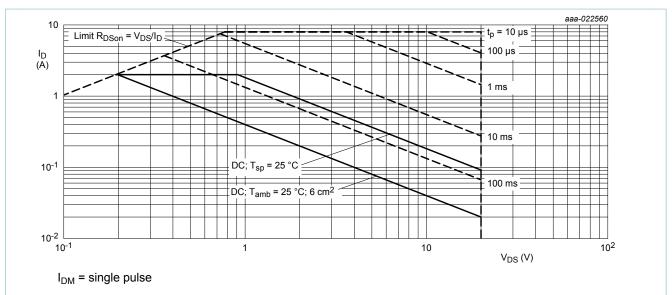


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fron	thermal resistance	in free air	[1]	-	363	418	K/W
	from junction to ambient	[2]	-	276	317	K/W	
	ambient	in free air; t ≤ 5 s	[2]	-	238	273	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	60	69	K/W

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

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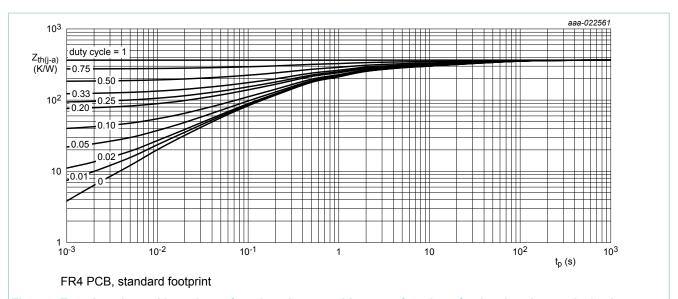


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

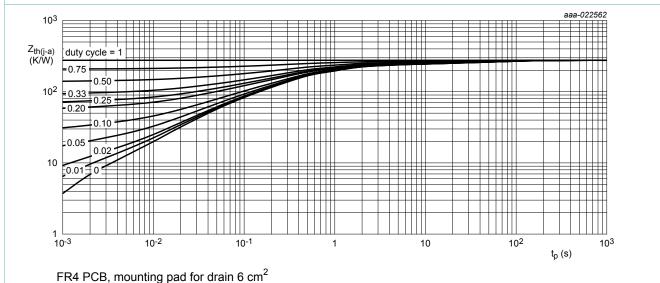


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = 250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	0.45	0.7	1	V
I _{DSS}	drain leakage current	V _{DS} = 20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-5	μA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 2 A; T _j = 25 °C	-	57	65	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 2 A; T _j = 150 °C	-	84	96	mΩ
		V _{GS} = 2.5 V; I _D = 1.8 A; T _j = 25 °C	-	64	74	mΩ
		V_{GS} = 1.8 V; I_D = 0.8 A; T_j = 25 °C	-	78	88	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 5 \text{ V}; I_D = 2 \text{ A}; T_j = 25 \text{ °C}$	-	9	-	S
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	-	1.8	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 10 V; I_{D} = 2 A; V_{GS} = 4.5 V;	-	3.9	5.85	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.3	-	nC
Q_{GD}	gate-drain charge		-	0.9	-	nC
C _{iss}	input capacitance	$V_{DS} = 10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	289	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	51	-	pF
C _{rss}	reverse transfer capacitance		-	42	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 10 V; I _D = 2 A; V _{GS} = 4.5 V;	-	8	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	27	-	ns
t _{d(off)}	turn-off delay time		-	35	-	ns
t _f	fall time		-	19	-	ns
Source-drai	in diode	1	1	1	1	
V _{SD}	source-drain voltage	$I_S = 0.37 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.7	1.2	V
		The state of the s		1		1

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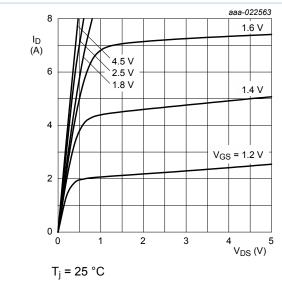


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

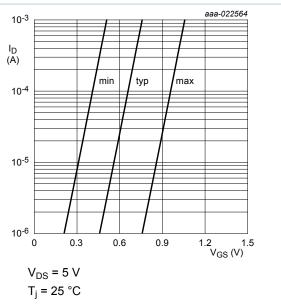


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

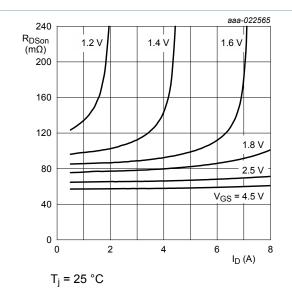


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

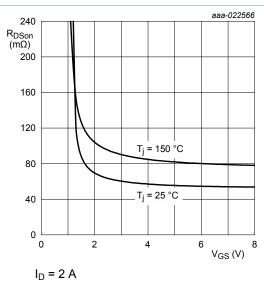


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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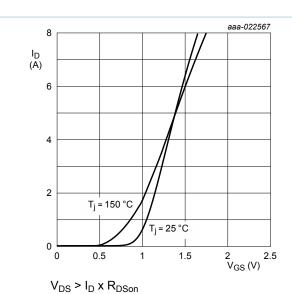


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

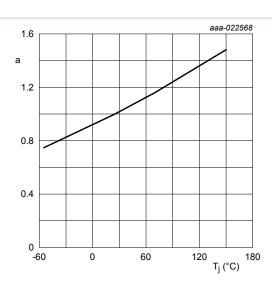


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

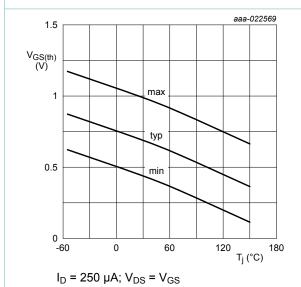


Fig. 12. Gate-source threshold voltage as a function of ambient temperature

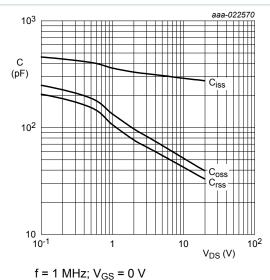


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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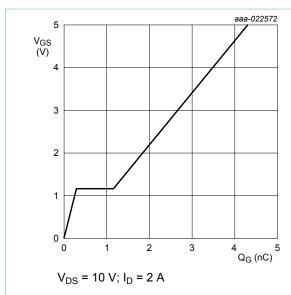


Fig. 14. Gate-source voltage as a function of gate charge; typical values

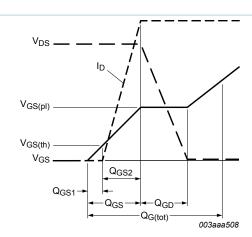


Fig. 15. Gate charge waveform definitions

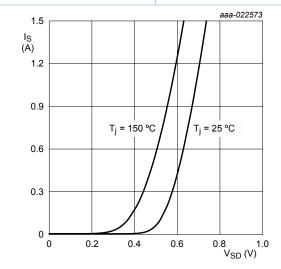
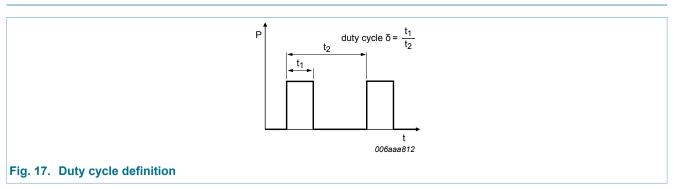


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



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12. Package outline

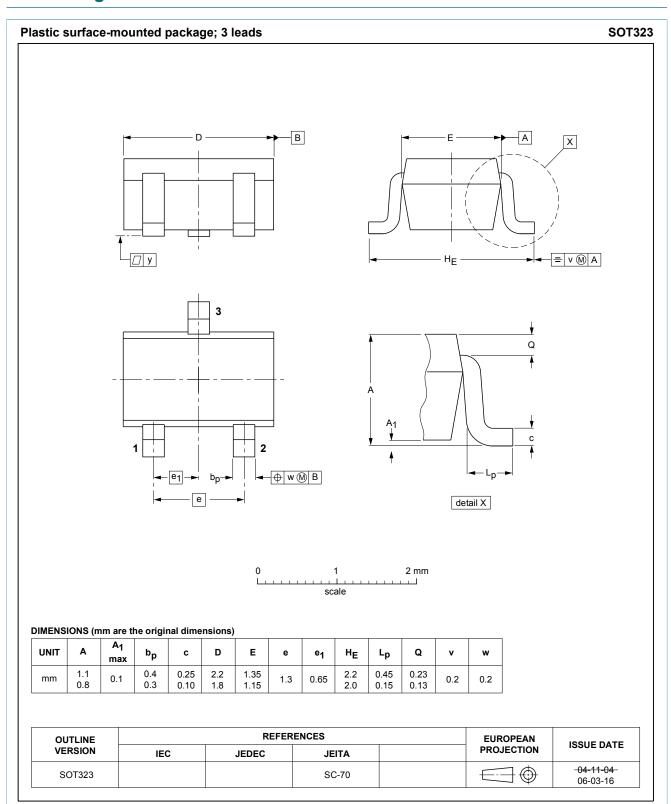
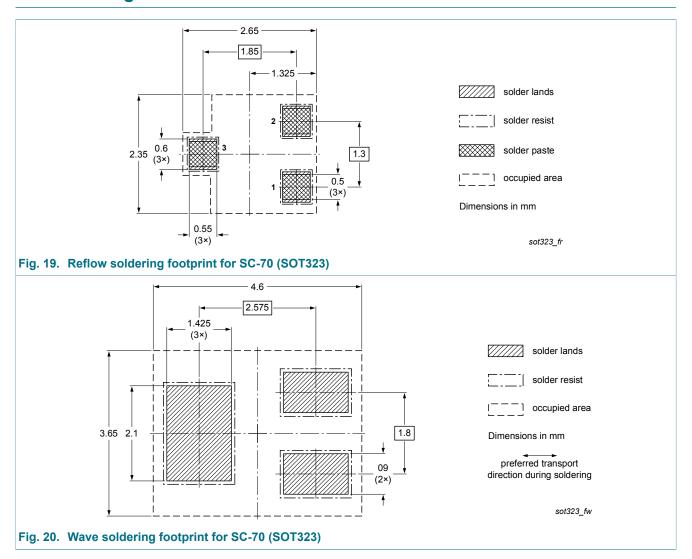


Fig. 18. Package outline SC-70 (SOT323)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMF63UNE v.1	20160420	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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